

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-343685

(43)Date of publication of application : 24.12.1993

(51)Int.Cl.

H01L 29/784

(21)Application number : 04-145714

(71)Applicant : FUJITSU LTD

(22)Date of filing : 05.06.1992

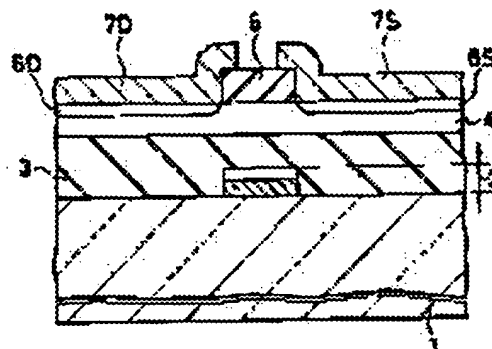
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## (54) MANUFACTURE OF SILICON THIN FILM TRANSISTOR

### (57)Abstract:

**PURPOSE:** To make possible the formation of a silicon film having a good crystallizability on an amorphous substrate consisting of glass or the like at a low temperature and to make it possible to realize easily a TFT having a high carrier mobility.

**CONSTITUTION:** A gate electrode 2 with at least the surface consisting of an ITO film is formed on a transparent insulative substrate 1 consisting of glass or the like and thereafter, a gate insulating film 3, which covers the electrode 2 and at the same time, is made to expose its Al surface and consists of an aluminium oxide film orientated to the face (012), is formed applying an atomic layer deposition method and a operating semiconductor layer 4 consisting of a silicon film having a good crystallizability is formed on the Al surface of the film 3 at a low temperature in a degree that the substrate 1 consisting of glass or the like is not softened.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the  
examiner's decision of rejection or application  
converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of  
rejection]

[Date of requesting appeal against examiner's decision  
of rejection]

[Date of extinction of right]